

SPEC SHEET (FOR REFERENCE)		Specification No.	Rev.	Page.	
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TYPE:6PT2810N3T**					
CHIP SIZE	1.4 * 1.4mm				
WAFER SIZE	6 inch				
Maximum Ratings (Ta=25°C)					
Characteristics	Symbol	Ratings	Unit		
Drain-Source voltage	VDSS	100	V		
Gate-Source voltage	VGSS	±20	V		
WAFER PROBING SPEC (Ta=25°C)					
No.	MODE	LIMIT			CONDITIONS
		MIN.	MAX.	UNIT	
1	IGSS	-	±15	uA	VGS= ±20V, VDS=0V
2	IDSS	-	100	nA	VDS= 100V, VGS=0V
3	BVDSS	110	-	V	ID= 10uA, VGS=0V
4	Vth	1.5	2.5	V	ID= 250uA, VGS=VDS
5	RDS(on) 1	0.15	0.3	ohm	ID= 2.0A, VGS=10V
6	RDS(on) 2	0.2	0.35	ohm	ID= 1.0A, VGS=4.5V
7	VSD	0.5	1.1	V	IS=1A, VGS= 0V
8	Yfs	500	-	mS	VDS= 10V, ID= 200mA
※Built in ZD between Gate and Source					

PHENITEC SEMICONDUCTOR Corp.

